

Spin Hall effect in graphene due to random Rashba field

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Spin Hall effect due to random Rashba spin-orbit coupling in the two-dimensional honeycomb lattice of carbon atoms (graphen) is considered theoretically. Using the Green function method and diagrammatic technique we show that fluctuations of the Rashba interaction around zero average value give rise to nonzero spin Hall conductivity. Generally, the conductivity is not universal, but depends on the ratio of the total momentum and spin-flip relaxation rates.

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Introduction: Interest in the phenomena due to spin-orbit coupling has revived in recent years owing to the possibility of pure electrical control of the spin degree of freedom. One of such phenomena is the spin Hall effect (SHE), predicted by Dyakonov and Perel in 1971¹⁻³. The effect consists in a spin current (or spin accumulation) flowing perpendicularly to an external electric field in systems with strong spin-orbit interaction. Of particular interest is the SHE in nonmagnetic systems, where the induced spin current is not accompanied by a charge current. Physical mechanisms that lead to SHE are either of intrinsic or extrinsic origin (for review see refs 4-7). The intrinsic SHE is associated with band structure modified by an intrinsic spin-orbit coupling of the material under consideration, and is a consequence of an unusual trajectory of electrons in the momentum space. Extrinsic contribution to the SHE, in turn, is a consequence of spin-orbit interaction due to impurities and other structural defects that lead to spin-dependent scattering – skew scattering and side jump.

In a general case, spin-orbit coupling in a system contains regular (spatially uniform or periodic) and random components⁸. Local imperfections of the system, like random distribution of donors or impurities, may lead to local enhancement/suppression of the regular spin-orbit coupling and as a consequence charge carriers in the system propagate in an effective fluctuating spin-orbit field. Such fluctuations of spin-orbit field strongly modify spin relaxation and significantly affect spin transport. Dugaev et al⁹ reported recently that the random Rashba field in two-dimensional electron gas generates nonzero SHE, even in the presence of potential scattering by impurities. This is distinct from the well known result for a two-dimensional electron gas with constant Rashba coupling, where potential scattering by impurities cancels out the universal intrinsic spin Hall conductivity^{10,11}.

In this paper we consider SHE created by fluctuating Rashba spin-orbit coupling in graphene – a two-dimensional honeycomb lattice of carbon atoms^{12,13}. The corresponding intrinsic spin-orbit coupling in graphene is very weak¹⁴, so the quantized value of spin Hall conductivity¹⁵, that appears inside the spin-orbit energy gap, is extremely difficult to be verified experimentally. In

turn, the Rashba type spin-orbit interaction in graphene appears generally due to a substrate and can be relatively strong. This interaction includes usually a regular component, but a random term may also appear due to ripples of the graphene plane, disorder, electron-phonon coupling in the substrate, presence of adatoms, etc¹⁶⁻¹⁹. The influence of fluctuating Rashba field on spin relaxation in graphene has been analyzed for two different models of the Rashba field fluctuations^{18,20}. Here we show that the spin Hall conductivity associated with such fluctuations is not universal and depends on the ratio of total momentum and spin relaxation times. We consider two different types of the correlation function for the spin-orbit coupling strength. Below, we briefly describe the model under consideration and the theoretical method used to calculate spin Hall conductivity. Then, we calculate the Feynman diagrams representing various contributions to the conductivity and also evaluate the spin dephasing time.

Model and method: Since the intrinsic spin-orbit interaction in a free standing graphene is very small, it will be neglected in the following. Accordingly, the low-energy electronic states around the Dirac point K are described by the Hamiltonian¹⁵ H_0^K , which in the sublattice space takes the matrix form

$$H_0^K = \begin{pmatrix} 0 & v(k_x - ik_y) \\ v(k_x + ik_y) & 0 \end{pmatrix}, \quad (1)$$

where $k_{x(y)}$ are the wavevector components, and $v = \hbar v_F$ with v_F being the electron Fermi velocity.

As already mentioned above, an important spin-orbit interaction in graphene is the Rashba coupling due to a substrate – though a related interaction may also appear in a free standing graphene with ripples. In the following we consider the case when the Rashba coupling vanishes on average, but the corresponding coupling parameter fluctuates in space around zero. These fluctuations of the Rashba field will be treated as a perturbation, so the full Hamiltonian for the point K can be written as $H^K = H_0^K + V_{\mathbf{k},\mathbf{k}'}^K$, where the perturbation $V_{\mathbf{k},\mathbf{k}'}^K$ takes the form

$$V_{\mathbf{k},\mathbf{k}'}^K = \begin{pmatrix} 0 & \lambda_{\mathbf{k}\mathbf{k}'}(\sigma_y + i\sigma_x) \\ \lambda_{\mathbf{k}\mathbf{k}'}(\sigma_y - i\sigma_x) & 0 \end{pmatrix}, \quad (2)$$

with $\lambda_{\mathbf{k}\mathbf{k}'}$ describing the corresponding Rashba coupling term, and σ_α ($\alpha = x, y, z$) being the Pauli matrices in spin space. According to our assumptions, $\langle \lambda_{\mathbf{q}} \rangle = 0$ and $\langle \lambda_{\mathbf{q}}^2 \rangle = C_{\mathbf{q}} \neq 0$ for $\mathbf{q} = \mathbf{k} - \mathbf{k}'$.

Following the Kubo-Streda formula^{21,22}, we write the spin Hall conductivity in the form

$$\sigma_{xy}^{s_z} = \sigma_{xy}^{s_z I} + \sigma_{xy}^{s_z II}. \quad (3)$$

The term $\sigma_{xy}^{s_z II}$ is the so-called topological contribution to the spin Hall conductivity, which comes from states below the Fermi level. This contribution, however, is equal to zero for the model under consideration ($\sigma_{xy}^{s_z II} \neq 0$ only inside the energy gap induced by intrinsic spin-orbit interaction, which has been neglected here). In turn, the term $\sigma_{xy}^{s_z I}$ is determined by states at the Fermi level and is given by the formula

$$\sigma_{xy}^{s_z I} = \frac{e\hbar}{2\pi} \int \frac{d^2\mathbf{k}}{(2\pi)^2} \text{Tr} \{ \hat{j}_x^{s_z} G^R(\varepsilon_F) \hat{v}_y G^A(\varepsilon_F) \}, \quad (4)$$

where $G_{\mathbf{k}}^{R(A)}(\varepsilon_F)$ is the retarded (advanced) Green function at the Fermi level ε_F ; $\hat{j}_x^{s_z} = (1/2)[v_x, s_z]_+$ is the spin current density operator, and $v_i = (1/\hbar)(\partial H / \partial k_i)$ is the velocity operator. In the model under consideration, $\hat{j}_x^{s_z}$ and v_y take the following explicit forms:

$$j_x^{s_z} = \frac{v}{2} \begin{pmatrix} 0 & \sigma_z \\ \sigma_z & 0 \end{pmatrix} \quad (5)$$

and

$$v_y = i \frac{v}{\hbar} \begin{pmatrix} 0 & -\sigma_0 \\ \sigma_0 & 0 \end{pmatrix}, \quad (6)$$

where σ_0 is a unit matrix in the spin space.

Spin Hall conductivity and spin relaxation: Perturbation expansion for the Green functions in Eq.(4) leads to a series of Feynman diagrams contributing to the spin Hall conductivity (see Fig.1). Thus, one can write

$$\sigma_{xy}^{s_z} = \frac{e\hbar}{2\pi} \text{Tr} \sum_{\mathbf{k}\mathbf{k}'} \sum_{n=1}^4 D_n \equiv \sigma_{xy}^{s_z(1)} + \sigma_{xy}^{s_z(2)} + \sigma_{xy}^{s_z(3+4)}. \quad (7)$$

The term $\sigma_{xy}^{s_z(1)}$ represents a contribution from the bare bubble diagram and is generally a part of intrinsic spin Hall conductivity. Since the nonperturbative part of the Hamiltonian does not contain any term associated with spin-orbit interaction, this term vanishes, $\sigma_{xy}^{s_z(1)} = 0$. The second term in Eq.(7) can be written as

$$\sigma_{xy}^{s_z(2)} = \frac{e\hbar}{2\pi} \int \frac{d^2\mathbf{k}}{(2\pi)^2} \frac{d^2\mathbf{k}'}{(2\pi)^2} \times \text{Tr} [j_x^{s_z} G_{\mathbf{k}}^R V_{\mathbf{k}\mathbf{k}'} G_{\mathbf{k}'}^R v_y G_{\mathbf{k}'}^A V_{\mathbf{k}'\mathbf{k}} G_{\mathbf{k}}^A]. \quad (8)$$

In turn, the last term of Eq.(7), corresponding to the bottom diagrams in Fig.1, takes the form

$$\sigma_{xy}^{s_z(3+4)} = \frac{e\hbar}{2\pi} \int \frac{d^2\mathbf{k}}{(2\pi)^2} \frac{d^2\mathbf{k}'}{(2\pi)^2} \times \text{Tr} [j_x^{s_z} G_{\mathbf{k}}^R v_y G_{\mathbf{k}}^A V_{\mathbf{k}\mathbf{k}'} G_{\mathbf{k}'}^A V_{\mathbf{k}'\mathbf{k}} G_{\mathbf{k}}^A + j_x^{s_z} G_{\mathbf{k}}^R V_{\mathbf{k}\mathbf{k}'} G_{\mathbf{k}'}^R V_{\mathbf{k}'\mathbf{k}} G_{\mathbf{k}}^R v_y G_{\mathbf{k}}^A]. \quad (9)$$

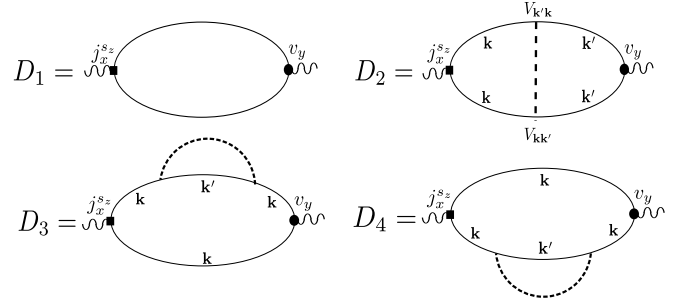


FIG. 1. Feynman diagrams corresponding to various contributions to the spin Hall conductivity in the dc limit.

The Green functions $G_{\mathbf{k}}^{R(A)}$ have the form, $G_{\mathbf{k}}^{R(A)} = [(\varepsilon_F \pm i\Gamma) - H_0^K]^{-1}$, where $\Gamma = \hbar/2\tau$. We assume that τ is the total relaxation time, which includes scattering from impurities, τ_i , and scattering from random Rashba field, τ_s . Thus one can write $1/\tau = 1/\tau_i + 1/\tau_s$. Note that for small impurity density the scattering from random Rashba field is the dominant mechanism of relaxation ($\tau \rightarrow \tau_s$). To obtain τ_s we calculate the self energy,

$$\Sigma^R = \int \frac{d^2\mathbf{k}'}{(2\pi)^2} V_{\mathbf{k}\mathbf{k}'} G_{\mathbf{k}'}^{0R} V_{\mathbf{k}'\mathbf{k}}. \quad (10)$$

Taking into account the explicit form of the Green function $G_{\mathbf{k}'}^{0R}$ corresponding to the Hamiltonian (1), one obtains

$$\Sigma^R = 4\varepsilon_F M \int \frac{d^2\mathbf{k}'}{(2\pi)^2} \frac{\langle \lambda_{\mathbf{k}\mathbf{k}'}^2 \rangle}{(\varepsilon_F - E_{1\mathbf{k}'} + i0^+)(\varepsilon_F - E_{2\mathbf{k}'} + i0^+)}, \quad (11)$$

where $E_{1,2} = \pm vk \equiv \pm \varepsilon_{\mathbf{k}}$, and

$$M = \begin{pmatrix} \frac{1}{2}(\sigma_0 - \sigma_z) & 0 \\ 0 & \frac{1}{2}(\sigma_0 + \sigma_z) \end{pmatrix}. \quad (12)$$

From the above equations follows that the self energy can be written as

$$\begin{aligned} \Sigma^R &= -i \frac{M}{2\pi} \int dq \, q \int d\theta \, C_q \delta(\varepsilon_F - \varepsilon_{\mathbf{k}-\mathbf{q}}) \\ &= -iM \frac{k_F}{\pi v} \int_0^{2k_F} dq \frac{2C_q}{\sqrt{4k_F^2 - q^2}}, \end{aligned}$$

or equivalently

$$\Sigma^R = -i\Gamma_s M, \quad (13)$$

where $\Gamma_s = \hbar/2\tau_s$. From Eq.(13) follows that the explicit form of τ_s depends on the form of the correlator C_q ^{18,20}.

Let us go now back to Eq.(8), which can be rewritten as

$$\begin{aligned} \sigma_{xy}^{s_z(2)} &= \frac{e}{2\pi} \int \frac{d^2\mathbf{k}}{(2\pi)^2} \frac{d^2\mathbf{k}'}{(2\pi)^2} \\ &\quad \frac{16|\lambda_{\mathbf{k}\mathbf{k}'}|^2 v^4 (k_x k'_x - k_y k'_y) \varepsilon_F \Gamma}{(\varepsilon_{\mathbf{k}}^2 - (\varepsilon_F - i\Gamma)^2)(\varepsilon_{\mathbf{k}'}^2 - (\varepsilon_F - i\Gamma)^2)} \\ &\quad \times \frac{1}{(\varepsilon_{\mathbf{k}}^2 - (\varepsilon_F + i\Gamma)^2)(\varepsilon_{\mathbf{k}'}^2 - (\varepsilon_F + i\Gamma)^2)}. \quad (14) \end{aligned}$$

Evaluation of this formula gives $\sigma_{xy}^{sz(2)} = 0$. Thus, the spin Hall conductivity is given by the bottom diagrams in Fig.1, $\sigma_{xy}^{sz} = \sigma_{xy}^{sz(3+4)}$, and for weak disorder one finds

$$\sigma_{xy}^{sz} = \frac{e}{4\pi^2} \frac{v^2 \varepsilon_F}{\Gamma} \int dq q \int dk k \times \int d\theta C_q \delta(\varepsilon_{\mathbf{k}}^2 - \varepsilon_F^2) \delta(\varepsilon_{\mathbf{k}-\mathbf{q}}^2 - \varepsilon_F^2). \quad (15)$$

Finally the spin Hall conductivity can be written in the following simple form:

$$\sigma_{xy}^{sz} = \frac{e}{4\pi^2} \frac{\varepsilon_F}{\Gamma} \int_0^{2k_F} dq \frac{C_q}{v^2 \sqrt{4k_F^2 - q^2}}. \quad (16)$$

Taking into account the formula for spin relaxation time, and including contributions from both K-points, we may write the formula for spin Hall conductivity in the form,

$$\sigma_{xy}^{sz} = \frac{e}{4\pi} \frac{\tau}{\tau_s}. \quad (17)$$

This formula clearly shows that SHE is generally not universal. Potential scattering by impurities reduces the spin Hall conductivity, but does not suppress it to zero.

The spin Hall conductivity depends on the form of the correlator C_q . Dugaev et al²⁰ assumed the correlator in the form

$$C_q^{(1)} = 2\pi \langle \lambda^2 \rangle R^2 e^{-qR}. \quad (18)$$

Such fluctuations may originate from the ripples or some impurities that exist at the surface of graphene. Using this correlator one obtains (for a single K point)

$$\sigma_{xy}^{sz} = \frac{e}{4\Gamma v} \langle \lambda^2 \rangle k_F R^2 (I_0(2k_F R) - L_0(2k_F R)), \quad (19)$$

where I_0 and L_0 are the modified Bessel and Struve functions of zeroth order, respectively. From this relation one finds a simple formula in some limiting cases,

$$\sigma_{xy}^{sz} = \frac{e}{4\pi} \frac{\langle \lambda^2 \rangle}{v\Gamma} R \begin{cases} \pi k_F R & ; k_F R \ll 1 \\ 1 & ; k_F R \gg 1 \end{cases}. \quad (20)$$

In turn, Zhang and Wu¹⁸ have proposed recently another form of the correlator that may describe fluctuations of the Rashba field due to the presence of adatoms distributed on top of the graphene surface and between the graphene layer and substrate,

$$C_q^{(2)} = 4\pi^2 n \langle \lambda^2 \rangle R^4 e^{-q^2 R^2}. \quad (21)$$

where n is the impurity density. The corresponding spin Hall conductivity (for single K point) takes the form

$$\sigma_{xy}^{sz} = \frac{en}{2v\Gamma} \langle \lambda^2 \rangle k_F R^4 \pi I_0(2k_F^2 R^2) e^{-2k_F^2 R^2}, \quad (22)$$

and in the limiting cases

$$\sigma_{xy}^{sz} = \frac{en}{2v\Gamma} \langle \lambda^2 \rangle R^3 \begin{cases} \pi k_F R & ; k_F R \ll 1 \\ \frac{\sqrt{\pi}}{2} & ; k_F R \gg 1 \end{cases}. \quad (23)$$

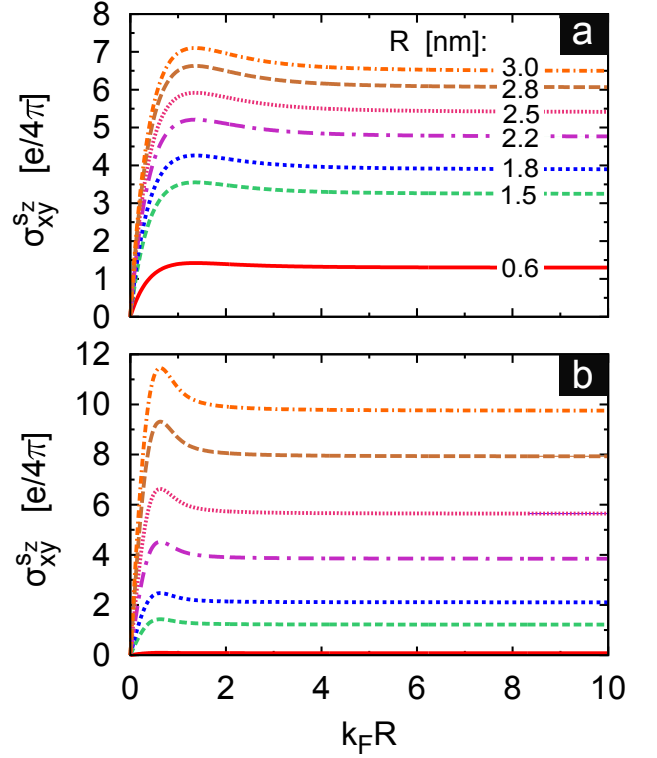


FIG. 2. Spin Hall conductivity as a function of $k_F R$ for constant (as indicated) values of R . The parts a) and b) correspond to the correlation function defined by Eq.(17) and Eq.(20), respectively. Contributions from both K points are included. The parameters used in the calculations are as follows: $\langle \lambda^2 \rangle = 25 \times 10^{-9} \text{ eV}^2$, $v = 3.516 \times 10^{-10} \text{ eV m}$, $n = 3 \times 10^{16} \text{ m}^{-2}$, and $\Gamma = 6.58 \times 10^{-8} \text{ eV}$.

Numerical results: Numerical results on the spin Hall conductivity in a general situation (arbitrary $k_F R$) are presented in Fig.2 and Fig.3. The contributions from both K and K' points are included there. Figure 2 shows the spin Hall conductivity as a function of $k_F R$ for fixed values of the correlation length R , as indicated. Parts (a) and (b) correspond to the two considered forms of the correlator C_q . In turn, Fig. 3 shows the spin Hall conductivity as a function of $k_F R$ in the case when k_F is fixed as indicated. As before, the upper and lower parts correspond to the two forms of the correlator C_q .

From these two figures clearly follows that the spin Hall conductivity vanishes when either the Fermi wavevector k_F or the correlation length R tend to zero. To understand this behavior one should bear in mind that $k_F = 0$ corresponds to the Fermi level at the Dirac points, where the density of states vanishes. In turn, the limit of $R = 0$ corresponds to the electron Fermi wavelength much longer than the scale length of the disorder. These limiting values of the spin Hall conductivity are in agreement with the corresponding formulas (20) and (23). When $k_F R$ grows (keeping R constant), the conductivity initially grows with $k_F R$ and after reaching maximum it tends to the limits for $k_F R \gg 1$ according

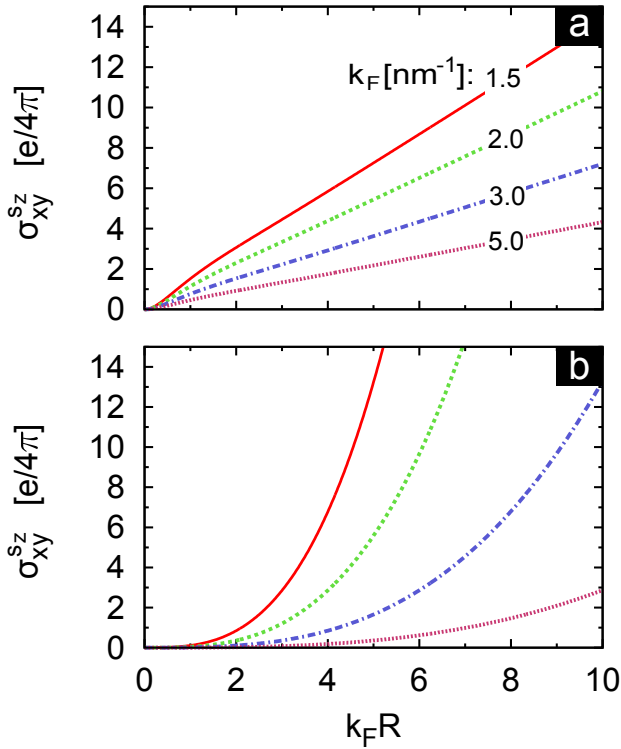


FIG. 3. Spin Hall conductivity as a function of $k_F R$ for constant (as indicated) values of k_F . The parts a) and b) correspond to the correlation function defined by Eq.(17) and Eq.(20), respectively. Contributions from both K points are included. The other parameters are as in Fig.2.

to the formulas (20) and (23). Note, these limits depend on R , as follows from (20) and (23). In turn, when k_F

is fixed (see Fig.3), the spin Hall conductivity increases with increasing $k_F R$, but the rate of this increase depends on k_F .

To conclude, we have analyzed the spin Hall effect induced by fluctuating Rashba spin-orbit interaction in a monolayer graphene. The key assumption was the absence of uniform Rashba term, i.e. the assumption that the Rashba interaction vanishes on average. Two different forms of the correlation function have been considered, which may correspond to different physical situations. We note, that such random Rashba interaction may appear as a result of ripples in a free standing graphene or due to impurities on both sides of the graphene plane.

It has been shown, that the spin Hall conductivity induced by the fluctuating Rashba field is equal to $(e/4\pi)(\tau/\tau_s)$, independently on the form of the correlator, and is generally not universal. A universal value occurs only when both τ and τ_s are equal (as in the absence of any other defects, except the fluctuating Rashba term). It is thus evident that potential scattering by defects suppresses the spin Hall effect, but this suppression is not complete, similarly as in the case of two-dimensional electron gas.

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- ¹ M. I. Dyakonov, V. I. Perel, Pis'ma Z. Eksp. Teor. Fiz. **13**, 657 (1971); JETP Lett. **13**, 467 (1971).
- ² M. I. Dyakonov, V. I. Perel, Phys. Lett. A **35**, 459 (1971).
- ³ J. E. Hirsch, Phys. Rev. Lett. **83**, 1834 (1999).
- ⁴ J. Schliemann, Int. J. Mod. Phys. B **20**, 1015 (2006).
- ⁵ A. Engel, E. I. Rashba, and B. I. Halperin, Theory of Spin Hall Effect in Semiconductors, in Handbook of Magnetism and Advanced Magnetic Materials, edited by H. Kronmüller and S. Parkin, Vol. 5, p.1 (John Wiley, New York 2007).
- ⁶ M. I. Dyakonov and A. V. Khaetskii, in Spin Physics in Semiconductors edited by M. I. Dyakonov Springer-Verlag, Berlin, Heidelberg, 2008, Chap. 8.
- ⁷ G. Vignale, J Supercond Nov Magn **23**, 3 (2010).
- ⁸ M. M. Glazov, E. Ya. Sherman, V. K. Dugaev, Physica E **42**, 2157 (2010).
- ⁹ V. K. Dugaev, M. Inglot, E. Ya. Sherman, and J. Barnas, Phys. Rev. B **82**, 121310(R) (2010).
- ¹⁰ J. Sinova, D. Culcer, Q. Niu, N. A. Synitsyn, T. Jungwirth and A. H. MacDonald, Phys. Rev. Lett. **92** 126603 (2004).
- ¹¹ J. Inoue, G. E. Bauer, L. W. Molenkamp, Phys. Rev. B **70**, 041303(R) (2004); E. G. Mishchenko, A. V. Shytov, and B. I. Halperin, Phys. Rev. Lett. **93**, 226602 (2004); R. Raimondi and P. Schwab, Phys. Rev. B **71**, 033311 (2005).
- ¹² A. K. Geim and K. S. Novoselov, Nature Mater. **6**, 183 (2007).
- ¹³ M. I. Katsnelson, Mater. Today **10**, 20 (2007).
- ¹⁴ M. Gmitra, S. Konschuh, C. Ertler, C. Ambrosch-Draxi, J. Fabian, Phys. Rev. B **80**, 235431 (2009).
- ¹⁵ C. L. Kane and E. J. Mele, Phys. Rev. Lett. **95**, 226801 (2005).
- ¹⁶ D. Huertas-Hernando, F. Guinea, A. Braatas, Eur. Phys. J. Special Topics **148**, 177 (2007).
- ¹⁷ C. Ertler, S. Konschuh, M. Gmitra, J. Fabian, Phys. Rev. B **80**, 041405 (2009).
- ¹⁸ P. Zhang, M. W. Wu, New J. Phys. **14**, 033015 (2012).
- ¹⁹ H. Jiang, Z. Qiao, H. Liu, J. Shi, Q. Niu, preprint arXiv:1204.3276.
- ²⁰ V. K. Dugaev, E. Ya Sherman and J. Barnas, Phys. Rev. B **83**, 085306 (2011).
- ²¹ P. Streda, J. Phys. C: Solid State Phys. **15**, L717 (1982).
- ²² M. F. Yang, M.-C. Chang, Phys. Rev. B **73**, 073304 (2006).